

SS8050 NPN Transistors

General description

SOT-23 Plastic-Encapsulate Transistors

SOT-23

FEATURES

• Complementary to SS8550

- Power Dissipation of 300mW
- High Stability and High Reliability

1. BASE 2. EMITTER 3. COLLECTOR



MECHANICAL DATA

- SOT-23 Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

Marking: Y1

Maximum Ratings & Thermal Characteristics T_A = 25°C unless otherwise noted

Parameters	Symbol	Value	Unit
Collector-Base Voltage	Vсво	40	V
Collector-Emitter Voltage	VCEO	25	V
Emitter -Base Voltage	VEBO	5	\ \
Collector Current-Continuous	Ic	1500	mA
Collector Power Dissipation	Pc	300	mW
Junction Temperature	Tj	150	$^{\circ}$ C
Storage Temperature	Tstg	-55-+150	$^{\circ}$ C
Thermal resistance From junction to ambient	Reja	417	°C/W

Electrical Characteristics T_A = 25°C unless otherwise noted

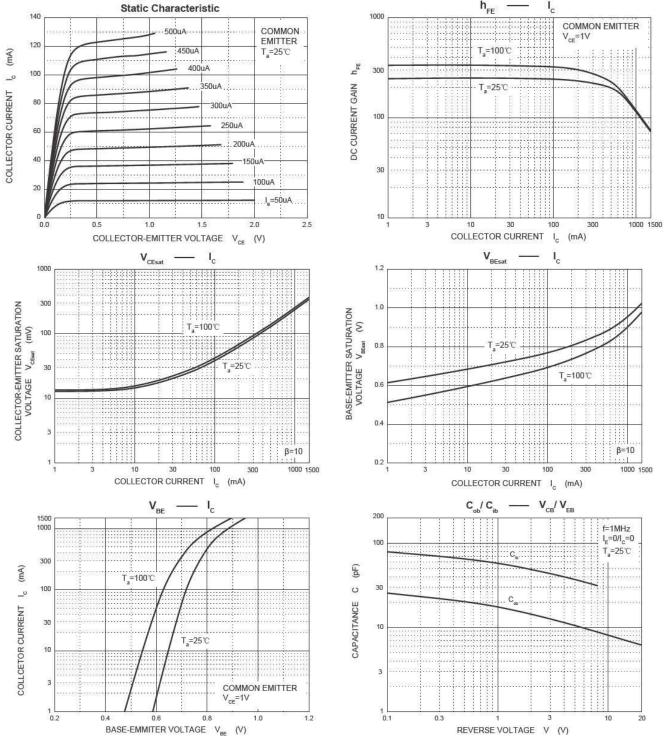
Parameter	Symbols	Test Condition	Limits		Unit
raiailletei	Symbols Test Condition		Min	Max	Oilit
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	40		V
Collector-emitter breakdown voltage	V(BR)CEO	IC=0.1mA, IB=0	25		V
Emitter-base breakdown voltage	V(BR)EBO	IE=100uA, IC=0	5		V
Collector cut-off current	ICEO	VCE=20V, IB=0		100	nA
Collector cut-off current	ICBO	VCB=40V, IE=0		100	nA
Emitter cut-off current	IEBO	VEB=5V, IC=0		100	nA
DC current gain	hFE(1)	VCE=1V, IC=100mA	120	400	
	hFE(2)	VCE=1V, IC=800mA	50		
Collector-emitter saturation voltage	VCE(sat)	IC=800mA, IB=80mA		0.60	V
Base -emitter saturation voltage	VBE(sat)	IC=800mA, IB=80mA		1.20	V
Transition frequency	fτ	VCE=10V, IC=50mA,f=30MHz	100		MHz

CLASSIFICATION OF hfe(1)

RANK	L	Н	J
RANGE	120-200	200-350	300-400

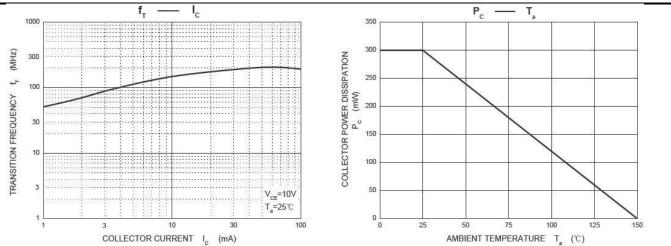




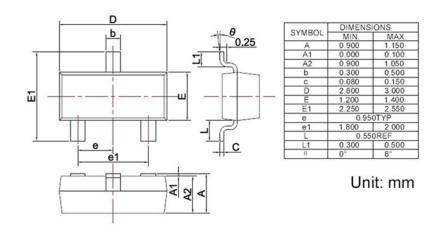


SS8050

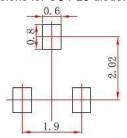




SOT-23 PACKAGE OUTLINE Plastic surface mounted package



Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
 1.Controlling dimension: in millilmeters,
 2.General tolerance: ± 0.05mm.
 3.The pad layout is for reference purposes only,



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